Erratum: Surface reconstructions of GaAs(100) observed by scanning tunneling microscopy [Phys. Rev. B 41, 5701 (1990)]

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In the article cited above, on page 5705, Fig. 4(a) was rotated 90° from the orientation of the actual STM data. The correct image is shown here:

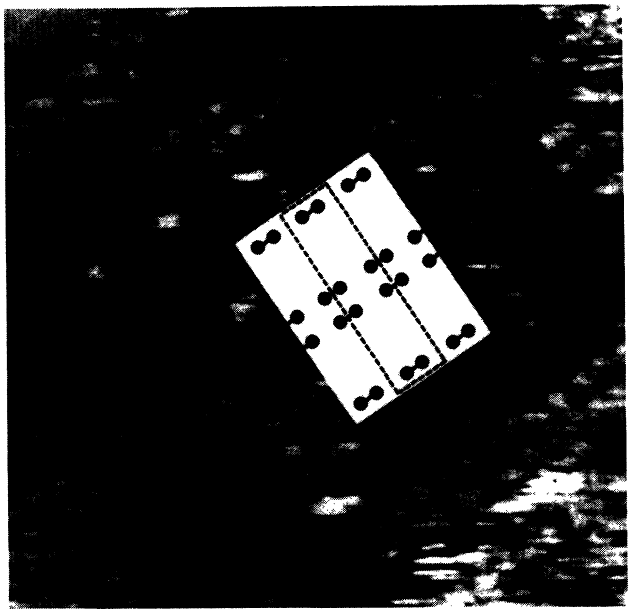

FIG. 4. (a) STM image of the GaAs(100) $c(8\times2)$ reconstruction. Inset shows unit cell and probable Ga-Ga dimerization.

Erratum: Strain effects in chemically lifted GaAs thin films [Phys. Rev. B 41, 7749 (1990)]

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The units of the hydrostatic and uniaxial deformation potentials *a* and *b* were incorrectly written as meV. The values reported are in fact in eV. This error occurs several times in the text, in Table I, and in the captions to Figs. 4 and 6. References to absorption energies, uncertainties and linewidths, and the spin-orbit splitting have the correct units.

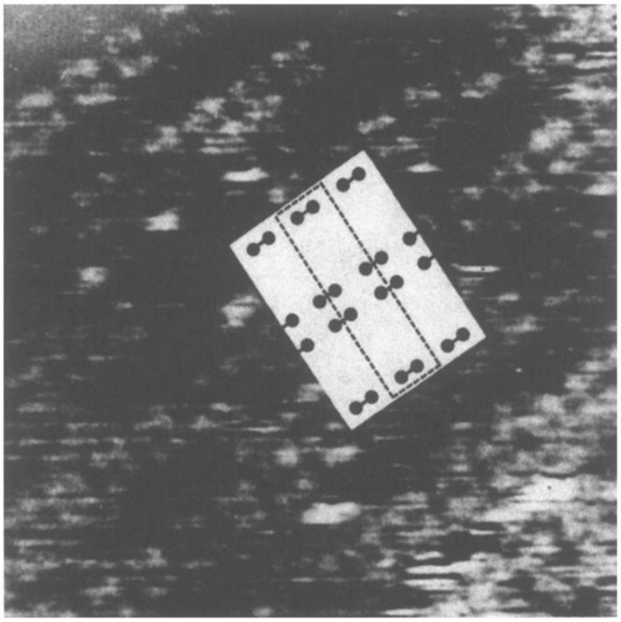

FIG. 4. (a) STM image of the GaAs(100) $c(8\times2)$ reconstruction. Inset shows unit cell and probable Ga-Ga dimerization.